

Small Signal Switching Diodes, High Voltage

- Features**

Silicon Epitaxial Planar Diodes
Lead (Pb)-free component



- Applications**

General purposes

- Mechanical Data**

Case: MiniMELF Glass case (SOD80)

Weight: approx. 31 mg

Cathode Band Color: Black



- Absolute Maximum Ratings**

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Repetitive peak reverse voltage		BAV100	V_{RRM}	60	V
		BAV101	V_{RRM}	120	V
		BAV102	V_{RRM}	200	V
		BAV103	V_{RRM}	250	V
Reverse voltage		BAV100	V_R	50	V
		BAV101	V_R	100	V
		BAV102	V_R	150	V
		BAV103	V_R	200	V
Peak forward surge current	$t_p = 1\text{ s}$		I_{FSM}	1	A
Repetitive peak forward current			I_{FRM}	625	mA
Forward continuous current			I_F	250	mA
Power dissipation			P_{tot}	500	mW

- Thermal Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction lead		R_{thJL}	350	K/W
Thermal resistance junction to ambient air	on PC board 50 mm x 50 mm x 1.6 mm	R_{thJA}	500	K/W
Junction temperature		T_J	175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 175	$^{\circ}\text{C}$

● Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 100\text{ mA}$		V_F			1000	mV
Reverse current	$V_R = 50\text{ V}$	BAV100	I_R			100	nA
	$V_R = 100\text{ V}$	BAV101	I_R			100	nA
	$V_R = 150\text{ V}$	BAV102	I_R			100	nA
	$V_R = 200\text{ V}$	BAV103	I_R			100	nA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 50\text{ V}$	BAV100	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 100\text{ V}$	BAV101	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 150\text{ V}$	BAV102	I_R			15	μA
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$, $t_p/T = 0.01$, $t_p = 0.3\text{ ms}$	BAV100	$V_{(BR)}$	60			V
	$I_R = 100\text{ }\mu\text{A}$, $t_p/T = 0.01$, $t_p = 0.3\text{ ms}$	BAV101	$V_{(BR)}$	120			V
	$I_R = 100\text{ }\mu\text{A}$, $t_p/T = 0.01$, $t_p = 0.3\text{ ms}$	BAV102	$V_{(BR)}$	200			V
	$I_R = 100\text{ }\mu\text{A}$, $t_p/T = 0.01$, $t_p = 0.3\text{ ms}$	BAV103	$V_{(BR)}$	250			V
Diode capacitance	$V_R = 0$, $f = 1\text{ MHz}$		C_D		1.5		pF
Differential forward resistance	$I_F = 10\text{ mA}$		r_f		5		Ω
Reverse recovery time	$I_F = I_R = 30\text{ mA}$, $i_R = 3\text{ mA}$, $R_L = 100\text{ }\Omega$		t_{rr}			50	ns

● Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

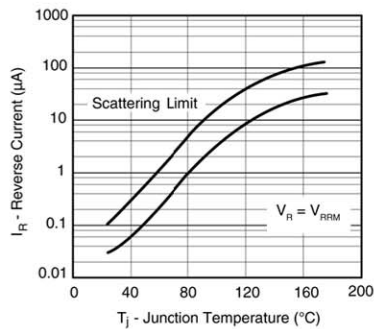


Figure 1. Reverse Current vs. Junction Temperature

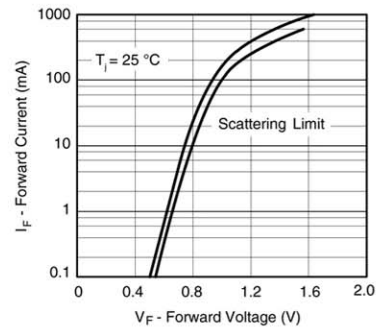


Figure 2. Forward Current vs. Forward Voltage

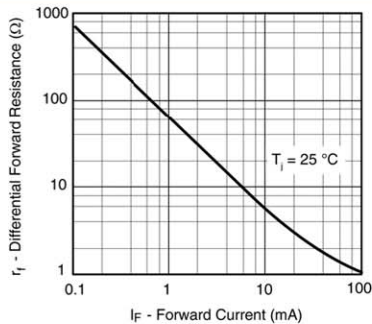
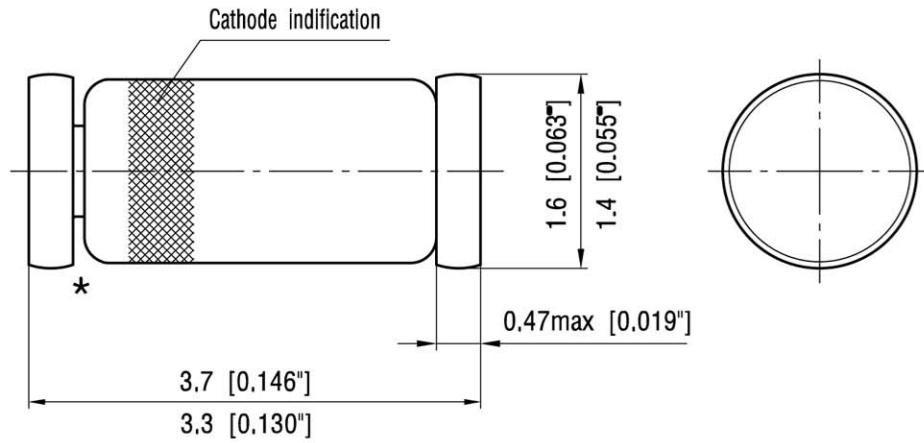


Figure 3. Differential Forward Resistance vs. Forward Current

Package Dimensions in millimeters (inches): SOD80



foot print recommendation:

